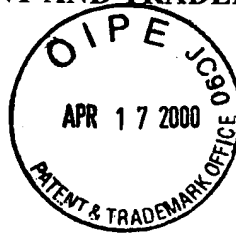


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



April 11, 2000

#7/A
la
4/20/00

In re Application of: Lo et al

Serial No. 09/247,413

Filed: 2/10/99

For: **METHOD FOR DESIGN OF EPITAXIAL LAYER AND
SUBSTRATE STRUCTURES FOR HIGH-QUALITY EPITAXIAL
GROWTH ON LATTICE-MISMATCHED SUBSTRATES**

Examiner: Anderson, M.

Art Unit: 1765

Attorney Docket No.: NOR-9

RECEIVED
APR 20 2000
TO 1700 MAIL ROOM

REPLY TO OFFICE ACTION

HONORABLE COMMISSIONER OF
PATENTS AND TRADEMARKS
Washington, D.C. 20231

In response to the Office Action dated January 7, 2000, please amend the above-
identified application as follows:

In the Claims:

Please amend claim 12 as follows:

12. (Amended) A method for forming low defect density epitaxial layers on lattice-mismatched
substrates, comprising the steps of:

a) choosing a first epilayer and a substrate for epitaxial growth;

CERTIFICATE OF CERTIFIED MAILING

CERTIFIED MAIL NO: 7099 3400 0012 4714 7947 **DATE:** 4-11-00

I hereby certify that this paper is being deposited with the U.S. Postal Service as Certified Mail
with return receipt requested in an envelope to Commissioner of Patents and Trademarks, Washington,
D.C. 20231.

Judy H. Barron
Judy H. Barron